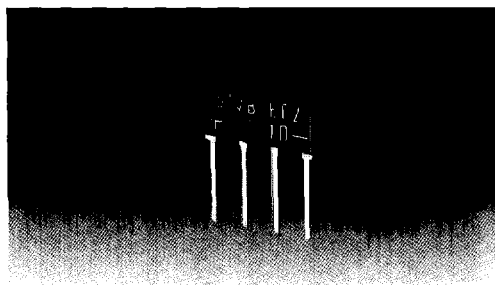
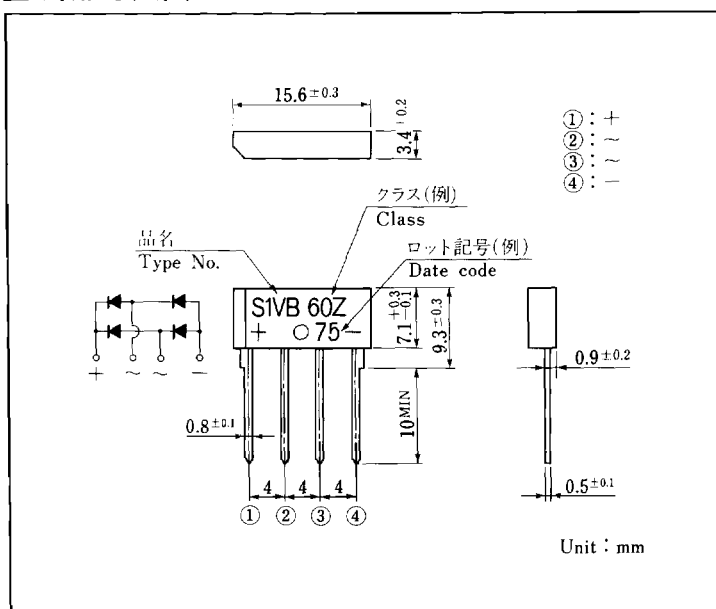


S1VB□Z

600V 1A



外形寸法図 OUTLINE DIMENSIONS



■ 定格表 RATINGS

絶対最大定格 Absolute Maximum Ratings

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.	S1VB60Z	単位 Unit
保存温度 Storage Temperature	Tstg			-40~150	°C
接合部温度 Operating Junction Temperature	Tj			150	°C
せん頭逆電圧 Maximum Reverse Voltage	VRM			600	V
出力電流 Average Rectified Forward Current	IO	50Hz正弦波, 抵抗負荷, プリント基板実装, Ta=25°C 50Hz sine wave, R-load, On glass-epoxy substrate, Ta=25°C		1	A
せん頭サージ順電流 Peak Surge Forward Current	IFSM	50Hz正弦波, 非繰り返し1サイクルせん頭値, Tj=25°C 50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25°C		30	A
電流2乗時間積 Current Squared Time	I²t	1ms ≤ t < 10ms Tc=25°C		2.5	A²s
せん頭サージ逆電力 Peak Surge Reverse Power	PRSM	パルス幅10μs, 非繰り返し, 1素子当り, Tj=25°C Pulse width 10μs, Non-repetitive, Rating of per diode, Tj=25°C		1	kW

電氣的・熱的特性 Electrical Characteristics (Tl=25°C)

順電圧 Forward Voltage	VF	IF=0.5A, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX 1.05	V
逆電流 Reverse Current	IR	VR=VRM, パルス測定, 1素子当りの規格値 Pulse measurement, Rating of per diode	MAX 10	μA
降伏電圧 Avalanche Voltage	VZ	IR=0.6mA, 1素子当りの規格値 Rating of per diode	MIN 750	V
熱抵抗 Thermal Resistance	θjl	接合部・リード間 Between junction and lead	MAX 16	°C/W
	θja	接合部・周囲間 Between junction and ambient	MAX 62	

■ 特性図 CHARACTERISTIC DIAGRAMS

